## Supporting Information

## Tunable Physical Properties in $BiAl_{1-x}Mn_xO_3$ Thin Films with Novel Layered Supercell Structures

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Target Mn%	Film Mn%	Bi	Al	Mn	Sr	Ті	0
33	40	8.51	4.49	2.84	12.19	13.94	58.03
50	55	8.82	3.09	3.75	12.24	13.91	58.19
67	67	6.37	1.82	3.78	13.56	14.88	59.59
80	80	8.17	1.24	5.21	12.89	14.15	58.33

**Table S1.** Composition of the film calculated using EDS in SEM.



Figure S1. XRD of BAO film deposited on CeO<sub>2</sub> buffered STO



**Figure S2.** A line scan across the pillars, showing the pillar to be *Al-rich*, formed within the  $BA_{1-x}M_xO(x=0.67)$  matrix.



**Figure S3.** XPS analysis of two extreme composition (a) x=0.4 and (b) x=0.8 showing the two possible Mn<sup>3+</sup> and Mn<sup>4+</sup> oxidation states.



Figure S4. PFM phase hysteresis loops for all the different thin films.